

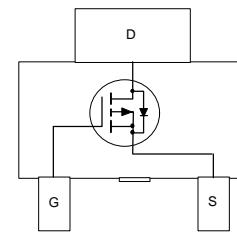
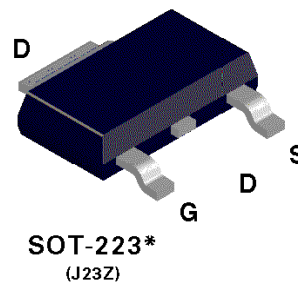
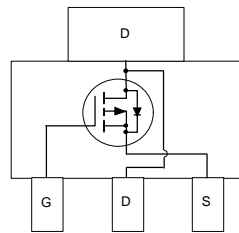
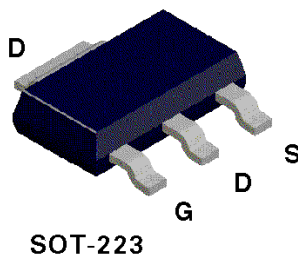
## NDT452AP P-Channel Enhancement Mode Field Effect Transistor

### General Description

Power SOT P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and DC motor control.

### Features

- -5A, -30V.  $R_{DS(ON)} = 0.065\Omega @ V_{GS} = -10V$   
 $R_{DS(ON)} = 0.1\Omega @ V_{GS} = -4.5V.$
- High density cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability in a widely used surface mount package.



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	NDT452AP	Units
$V_{DSS}$	Drain-Source Voltage	-30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current - Continuous (Note 1a)	-5	A
	- Pulsed	- 15	
$P_D$	Maximum Power Dissipation (Note 1a)	3	W
	(Note 1b)	1.3	
	(Note 1c)	1.1	
$T_J, T_{STG}$	Operating and Storage Temperature Range	-65 to 150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	42	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	12	$^\circ\text{C/W}$

\* Order option J23Z for cropped center drain lead.

**Electrical Characteristics** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$ $T_J = 55^\circ\text{C}$			-1	$\mu\text{A}$
					-10	$\mu\text{A}$
$I_{GSSF}$	Gate - Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate - Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
<b>ON CHARACTERISTICS</b> (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$ $T_J = 125^\circ\text{C}$	-1	-1.6	-2.8	V
			-0.7	-1.2	-2.2	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -5.0\text{ A}$ $T_J = 125^\circ\text{C}$ $V_{GS} = -4.5\text{ V}, I_D = -4.3\text{ A}$		0.052	0.065	$\Omega$
				0.075	0.13	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -10\text{ V}, V_{DS} = -5\text{ V}$ $V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-15			A
			-5			
$g_{FS}$	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -5.0\text{ A}$		7		S
<b>DYNAMIC CHARACTERISTICS</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		690		pF
$C_{oss}$	Output Capacitance			430		pF
$C_{rss}$	Reverse Transfer Capacitance			160		pF
<b>SWITCHING CHARACTERISTICS</b> (Note 2)						
$t_{D(on)}$	Turn - On Delay Time	$V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GEN} = -10\text{ V}, R_{GEN} = 6\ \Omega$		9	20	ns
$t_r$	Turn - On Rise Time			20	30	ns
$t_{D(off)}$	Turn - Off Delay Time			40	50	ns
$t_f$	Turn - Off Fall Time			19	40	ns
$Q_g$	Total Gate Charge		$V_{DS} = -10\text{ V},$ $I_D = -5.0\text{ A}, V_{GS} = -10\text{ V}$		22	30
$Q_{gs}$	Gate-Source Charge			3.2		nC
$Q_{gd}$	Gate-Drain Charge			5.2		nC

## Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-2.5	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -2.5 A (Note 2)		-0.85	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>F</sub> = -2.5 A, dI <sub>F</sub> /dt = 100 A/μs			100	ns

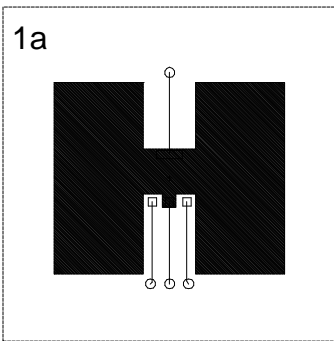
Notes:

- R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design.

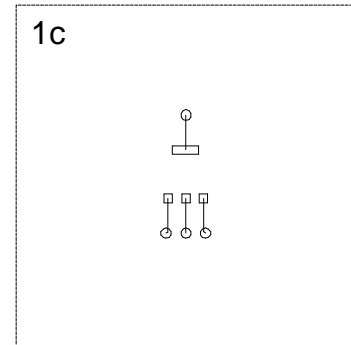
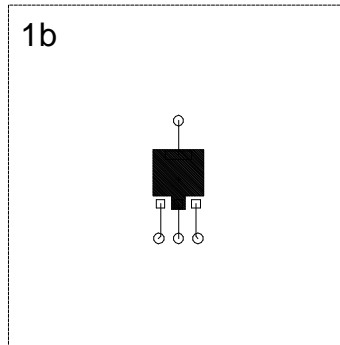
$$P_D(t) = \frac{T_J - T_A}{R_{\theta JA}(t)} = \frac{T_J - T_A}{R_{\theta JC} + R_{\theta CA}(t)} = I_D^2(t) \times R_{DS(ON)} \theta_{TJ}$$

Typical R<sub>θJA</sub> using the board layouts shown below on 4.5"x5" FR-4 PCB in a still air environment:

- 42°C/W when mounted on a 1 in<sup>2</sup> pad of 2oz copper.
- 95°C/W when mounted on a 0.066 in<sup>2</sup> pad of 2oz copper.
- 110°C/W when mounted on a 0.0123 in<sup>2</sup> pad of 2oz copper.



Scale 1 : 1 on letter size paper



- Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%.

## Typical Electrical Characteristics

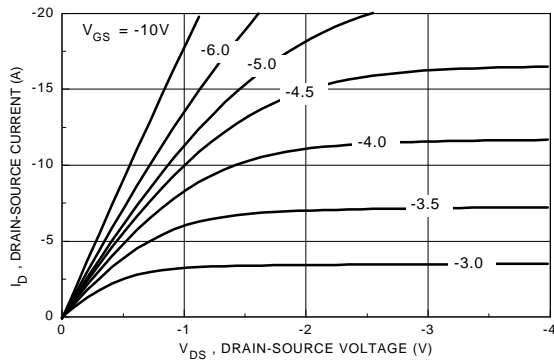


Figure 1. On-Region Characteristics.

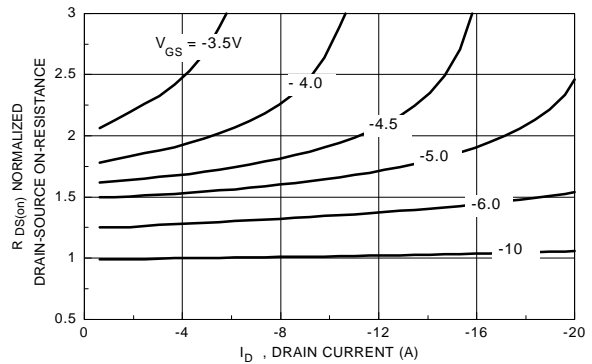


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

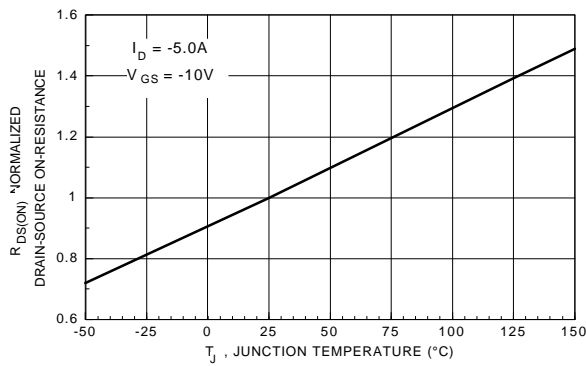


Figure 3. On-Resistance Variation with Temperature.

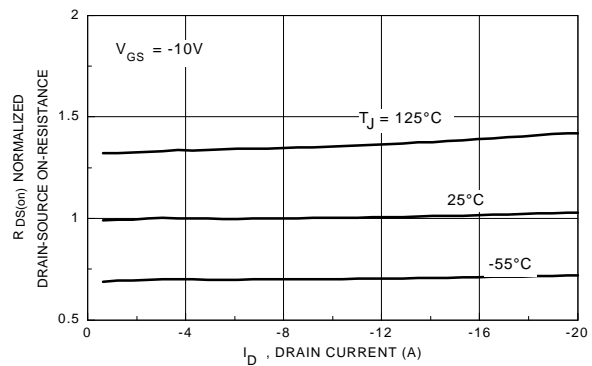


Figure 4. On-Resistance Variation with Drain Current and Temperature.

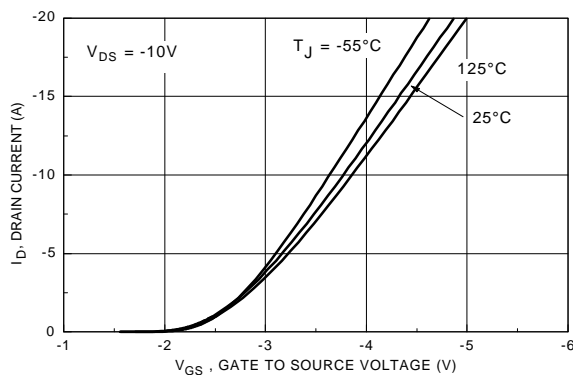


Figure 5. Transfer Characteristics.

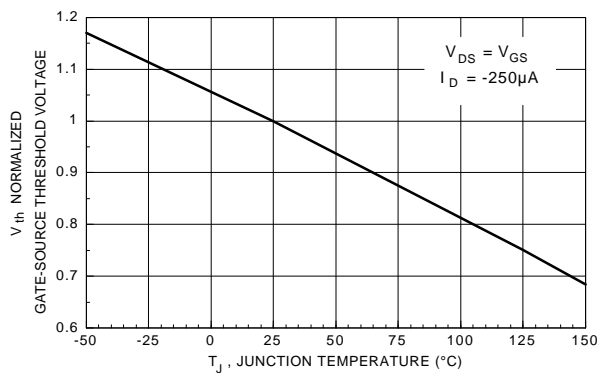
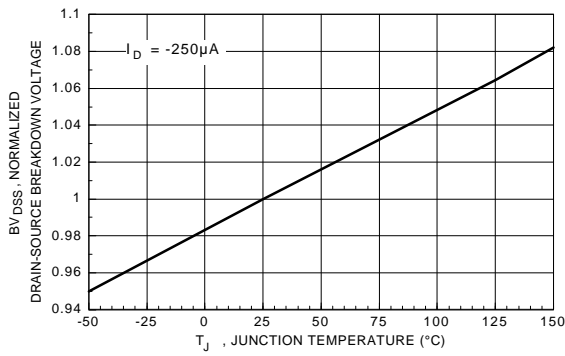
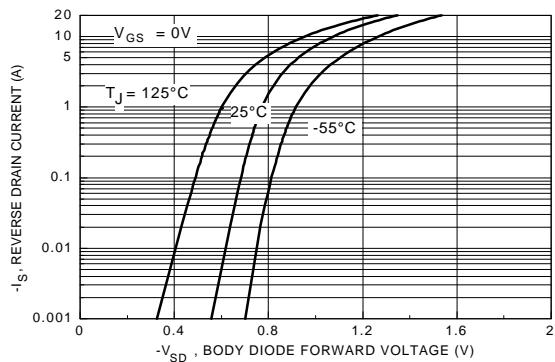


Figure 6. Gate Threshold Variation with Temperature.

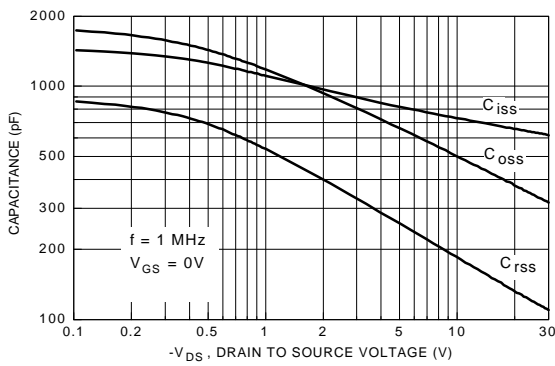
## Typical Electrical Characteristics



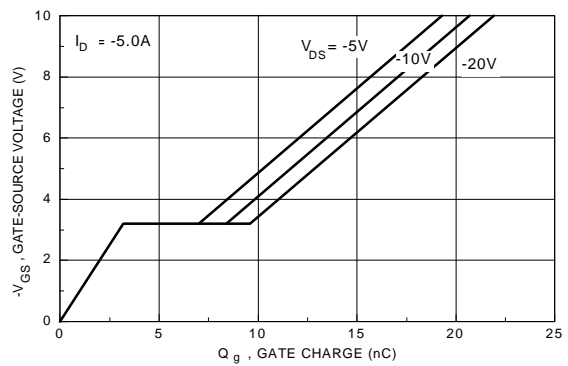
**Figure 7. Breakdown Voltage Variation with Temperature.**



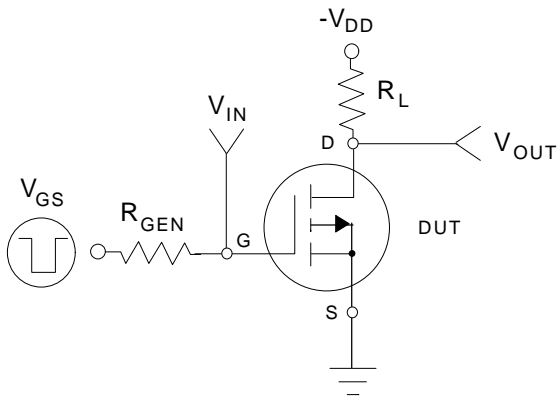
**Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.**



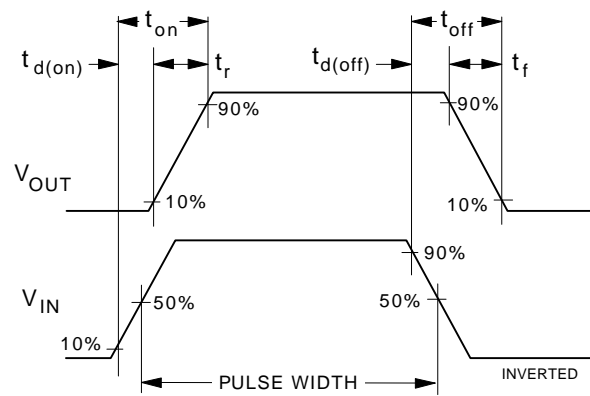
**Figure 9. Capacitance Characteristics.**



**Figure 10. Gate Charge Characteristics.**



**Figure 11. Switching Test Circuit.**



**Figure 12. Switching Waveforms.**

## Typical Thermal Characteristics

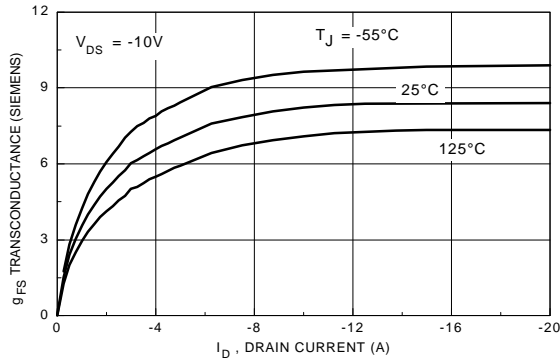


Figure 13. Transconductance Variation with Drain Current and Temperature.

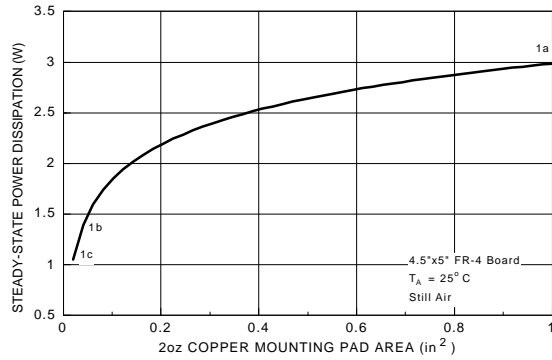


Figure 14. SOT-223 Maximum Steady-state Power Dissipation versus Copper Mounting Pad Area.

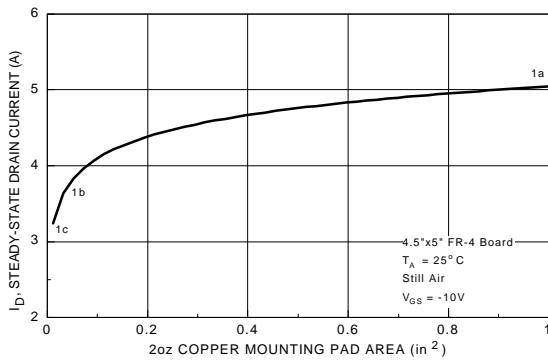


Figure 15. Maximum Steady-State Drain Current versus Copper Mounting Pad Area.

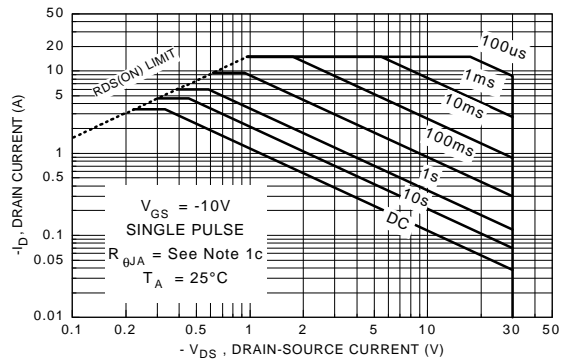


Figure 16. Maximum Safe Operating Area.

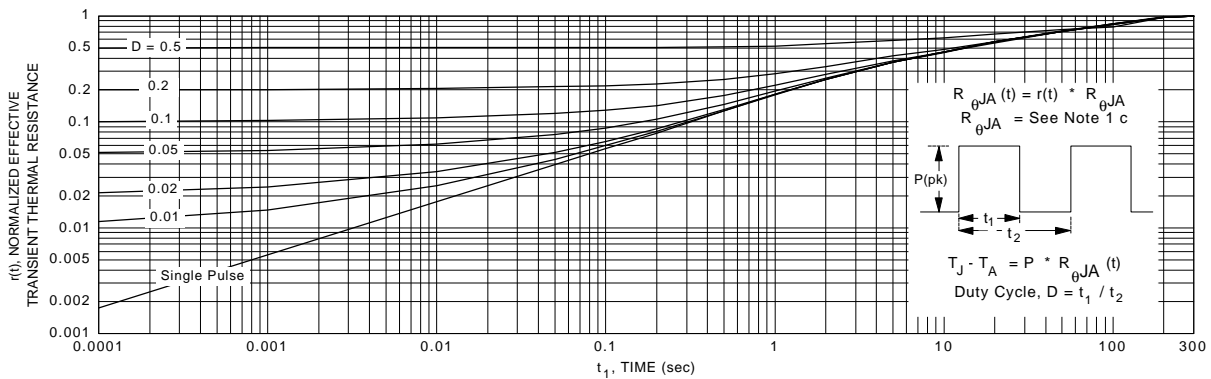


Figure 17. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c. Transient thermal response will change depending on the circuit board design.

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DenseTrench <sup>TM</sup>	GTO <sup>TM</sup>	Power247 <sup>TM</sup>	SuperSOT <sup>TM</sup> -6	
DOMET <sup>TM</sup>	HiSeC <sup>TM</sup>	PowerTrench <sup>®</sup>	SuperSOT <sup>TM</sup> -8	
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